

## Description

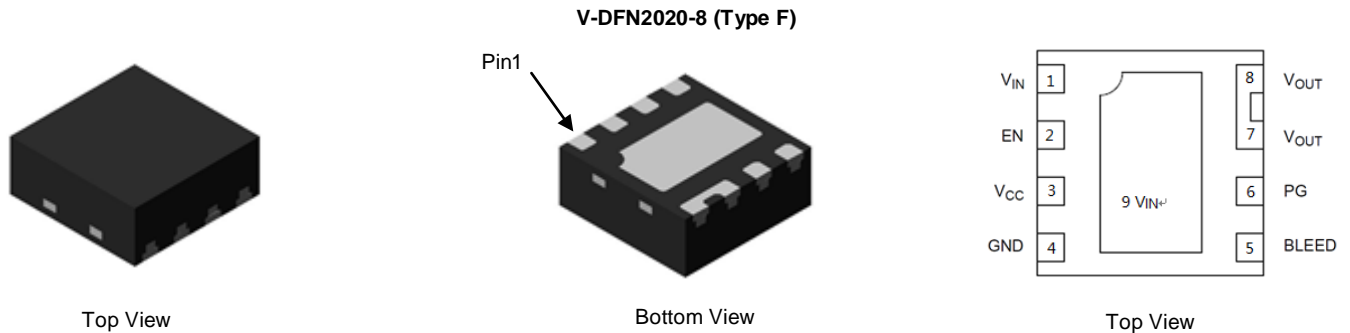
The DML3006LFDS load switch provides a component and area-reducing solution for efficient power domain switching with inrush current limit via soft-start. In addition to integrated control functionality with ultra-low on-resistance, this device offers system safeguards and monitoring via fault protection and power good signaling. This cost-effective solution is ideal for power management and hot-swap applications requiring low power consumption in a small footprint.

## Applications

- Portable Electronics and Systems
- Notebook and Tablet Computers
- Telecom, Networking, Medical, and Industrial Equipment
- Set-Top Boxes, Servers, and Gateways
- Hot-Swap Devices and Peripheral Ports

## Features and Benefits

- Advanced Controller with ChargePump
- Integrated N-Channel MOSFET with Ultra-Low  $R_{ON}$
- Input Voltage Range: 0.5V to 13.5V
- Soft-Start via Controlled SlewRate
- Power Good Signal
- Thermal Shutdown
- $V_{IN}$  Undervoltage Lockout
- Short-Circuit Protection
- Extremely Low Standby Current
- Load Bleed (QuickDischarge)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**



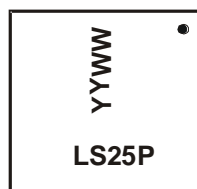
## Ordering Information (Note 4)

Part Number	Case	Packaging
DML3006LFDS-7	V-DFN2020-8 (Type F)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

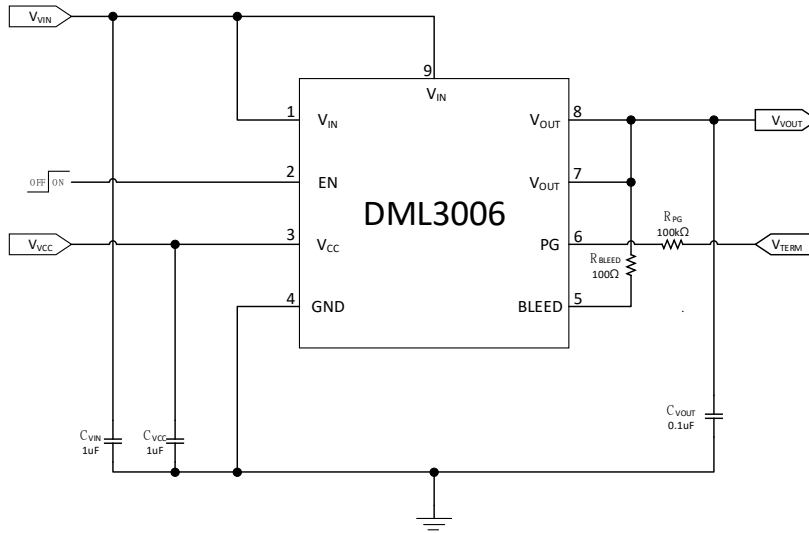
## Marking Information

### V-DFN2020-8 (Type F)



- LS25P = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 21 = 2021)
- WW = Week Code (01 to 53)

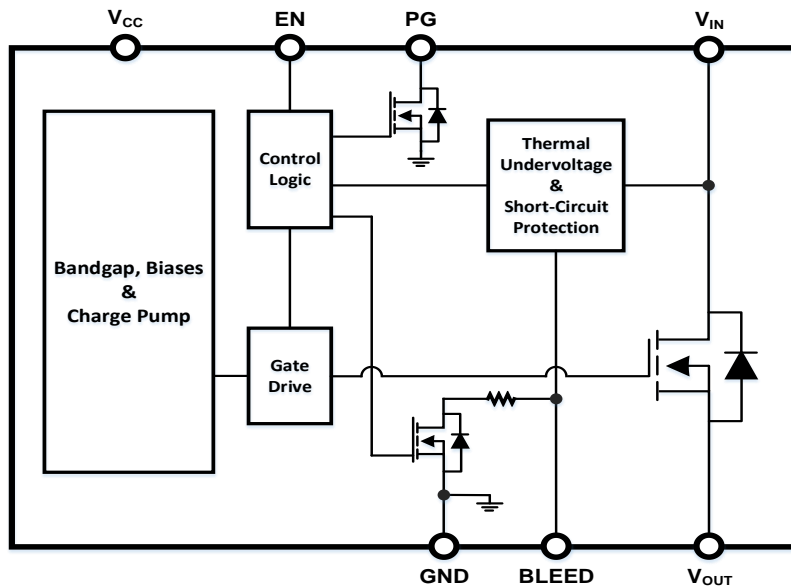
**Typical Applications Circuit**



**Pin Description**

Pin Number	Pin Name	Pin Function
1, 9	V <sub>IN</sub>	Drain of MOSFET (0.5V to 13.5V), Pin 1 must be connected to Pin 9
2	EN	Active-high digital input used to turn on the MOSFET, pin has an internal pull down resistor to GND
3	V <sub>CC</sub>	Supply voltage to controller (3.0V to 5.5V)
4	GND	Controller ground
5	BLEED	Load bleed connection, must be tied to V <sub>OUT</sub> through a resistor ≤ 1kΩ
6	PG	Active-high, open-drain output that indicates when the gate of the MOSFET is fully charged, external pull up resistor ≥1kΩ to an external voltage source required; tie to GND if not used.
7, 8	V <sub>OUT</sub>	Source of MOSFET connected to load

**Function Block Diagram**



### Absolute Maximum Ratings

Parameter	Rating
V <sub>IN</sub> , BLEED, V <sub>OUT</sub> to GND	-0.3V to 18V
EN, V <sub>CC</sub> , PG to GND	-0.3V to 6V
I <sub>MAX_DC</sub> *	11A
Junction Temperature (T <sub>J</sub> )	+150°C
Storage Temperature (T <sub>S</sub> )	-65°C to +150°C

\*I<sub>MAX\_DC</sub> is defined as the maximum steady state current the load switch can pass at room ambient temperature without entering thermal lockout.

### Recommended Operating Ranges

Parameter	Rating
Supply Voltage (V <sub>VCC</sub> )	3V to 5.5V
Input Voltage (V <sub>VIN</sub> )	0.5V to 13.5V
Ambient Temperature (T <sub>A</sub> )	-40°C to +85°C
Package Thermal Resistance (θ <sub>JC</sub> )	5.3°C/W
Package Thermal Resistance (θ <sub>JA</sub> )	40°C/W

### Electrical Characteristics (T<sub>A</sub> = +25°C, V<sub>VCC</sub>=3.3V, V<sub>VIN</sub>=5V=V<sub>TERM</sub>, C<sub>VIN</sub>=1μF, C<sub>VOUT</sub>=0.1μF, C<sub>VCC</sub>=1μF, C<sub>SR</sub>=1nF, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>VIN</sub>	Input Voltage	—	0.5	—	13.5	V
V <sub>VCC</sub>	Supply Voltage	—	3.0	—	5.5	V
I <sub>DYN</sub>	V <sub>CC</sub> Dynamic Supply Current	V <sub>EN</sub> = V <sub>VCC</sub> = 3V, V <sub>VIN</sub> = 12V	—	310	400	μA
		V <sub>EN</sub> = V <sub>VCC</sub> = 5.5V, V <sub>VIN</sub> = 1.8V	—	510	750	μA
I <sub>STBY</sub>	V <sub>CC</sub> Shutdown Supply Current	V <sub>VCC</sub> = 3V, V <sub>EN</sub> = 0V	—	0.1	1	μA
		V <sub>VCC</sub> = 5.5V, V <sub>EN</sub> = 0V	—	0.1	2	μA
V <sub>ENH</sub>	EN High Level Voltage	V <sub>VCC</sub> = 3V to 5.5V	2.0	—	—	V
V <sub>ENL</sub>	EN Low Level Voltage	V <sub>VCC</sub> = 3V to 5.5V	—	—	0.8	V
R <sub>BLEED</sub>	Bleed Resistance	V <sub>VCC</sub> = 3V, V <sub>EN</sub> = 0V	86	108	130	Ω
		V <sub>VCC</sub> = 5.5V, V <sub>EN</sub> = 0V	64	80	100	Ω
I <sub>BLEED</sub>	Bleed Pin Leakage Current	V <sub>VCC</sub> = V <sub>EN</sub> = 3V, V <sub>VIN</sub> = 1.8V	—	20	45	μA
		V <sub>VCC</sub> = V <sub>EN</sub> = 3V, V <sub>VIN</sub> = 12V	—	50	70	μA
V <sub>PGL</sub>	PG Output Low Voltage	V <sub>VCC</sub> = 3V; I <sub>SINK</sub> = 5mA	—	—	0.2	V
I <sub>PG</sub>	PG Output Leakage Current	V <sub>VCC</sub> = 3V; V <sub>TERM</sub> = 3.3V	—	—	100	nA
<b>Switching Device</b>						
R <sub>ON</sub>	Switch On-State Resistance	V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 1.8V	—	10.8	12.5	mΩ
		V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 5V	—	10.8	12.5	mΩ
		V <sub>VCC</sub> = 3.3V, V <sub>VIN</sub> = 12V	—	10.8	12.5	mΩ
		V <sub>VCC</sub> = 5V, V <sub>VIN</sub> = 1.8V	—	8.6	10.5	mΩ
		V <sub>VCC</sub> = 5V, V <sub>VIN</sub> = 5V	—	8.6	10.5	mΩ
		V <sub>VCC</sub> = 5V, V <sub>VIN</sub> = 12V	—	8.6	10.5	mΩ
I <sub>LEAK</sub>	Input Shutdown Supply Current	V <sub>EN</sub> = 0V, V <sub>VIN</sub> = 13.5V	—	—	1	μA
R <sub>PDEN</sub>	EN Pull Down Resistance	—	76	100	124	kΩ
<b>Fault Protection</b>						
OTP	Thermal Shutdown Threshold	V <sub>VCC</sub> = 3V to 5.5V	—	145	—	°C
OTP <sub>HYS</sub>	Thermal Shutdown Hysteresis	V <sub>VCC</sub> = 3V to 5.5V	—	20	—	°C
UVLO	V <sub>IN</sub> Lockout Threshold	V <sub>VCC</sub> = 3V	0.25	0.35	0.45	V
UVLO <sub>HYS</sub>	V <sub>IN</sub> Lockout Hysteresis	V <sub>VCC</sub> = 3V	20	40	70	mV
SCP	Short-Circuit Protection Threshold	V <sub>VCC</sub> = 3.3V; V <sub>VIN</sub> = 0.5V	180	265	350	mV
		V <sub>VCC</sub> = 3.3V; V <sub>VIN</sub> = 13.5V	100	285	500	mV

**Switching Characteristics** ( $T_A = +25^\circ\text{C}$ ,  $V_{\text{TERM}}=V_{\text{VCC}}=5\text{V}$ ,  $R_{\text{PG}}=100\text{k}\Omega$ ,  $R_{\text{VOUT}}=10\Omega$ ,  $C_{\text{VIN}}=1\mu\text{F}$ ,  $C_{\text{VOUT}}=0.1\mu\text{F}$ ,  $C_{\text{VCC}}=1\mu\text{F}$ , unless otherwise specified.)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b><math>V_{\text{VIN}} = 1.8\text{V}</math></b>						
$t_{\text{ON}}$	Output Turn-On Delay Time	$V_{\text{VCC}}=3.3\text{V}$	—	200	—	$\mu\text{s}$
		$V_{\text{VCC}}=5\text{V}$	—	190	—	
$t_{\text{OFF}}$	Output Turn-Off Delay Time	$V_{\text{VCC}}=3.3\text{V}$	—	0.4	—	$\mu\text{s}$
		$V_{\text{VCC}}=5\text{V}$	—	0.4	—	
$t_{\text{PGON}}$	Power Good Turn-on Time	$V_{\text{VCC}}=3.3\text{V}$	—	1.25	—	ms
		$V_{\text{VCC}}=5\text{V}$	—	1.05	—	
$t_{\text{PGOFF}}$	Power Good Turn-off Time	$V_{\text{VCC}}=3.3\text{V}$	—	10	—	ns
		$V_{\text{VCC}}=5\text{V}$	—	8	—	
SR	Output Slew Rate	$V_{\text{VCC}}=3.3\text{V}$	—	23	—	kV/s
		$V_{\text{VCC}}=5\text{V}$	—	24	—	
<b><math>V_{\text{VIN}} = 12\text{V}</math></b>						
$t_{\text{ON}}$	Output Turn-On Delay Time	$V_{\text{VCC}}=3.3\text{V}$	—	190	—	$\mu\text{s}$
		$V_{\text{VCC}}=5\text{V}$	—	180	—	
$t_{\text{OFF}}$	Output Turn-Off Delay Time	$V_{\text{VCC}}=3.3\text{V}$	—	0.4	—	$\mu\text{s}$
		$V_{\text{VCC}}=5\text{V}$	—	0.4	—	
$t_{\text{PGON}}$	Power Good Turn-On Time	$V_{\text{VCC}}=3.3\text{V}$	—	1.3	—	ms
		$V_{\text{VCC}}=5\text{V}$	—	1.25	—	
$t_{\text{PGOFF}}$	Power Good Turn-Off Time	$V_{\text{VCC}}=3.3\text{V}$	—	10	—	ns
		$V_{\text{VCC}}=5\text{V}$	—	8	—	
SR	Output Slew Rate	$V_{\text{VCC}}=3.3\text{V}$	—	80	—	kV/s
		$V_{\text{VCC}}=5\text{V}$	—	81	—	

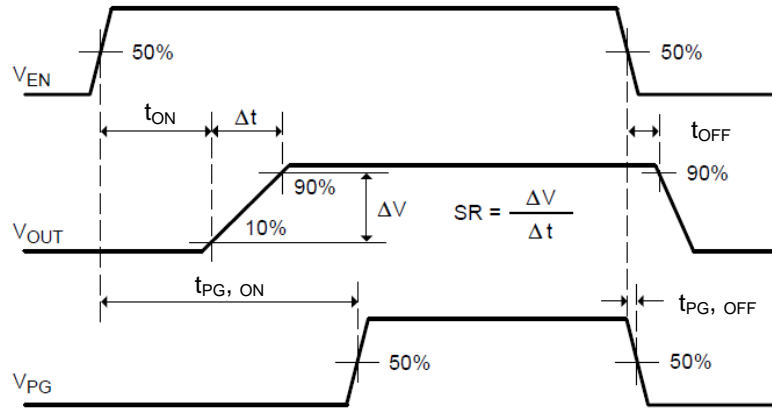
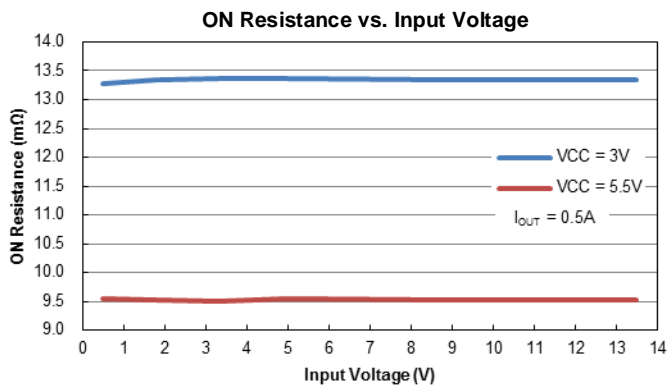
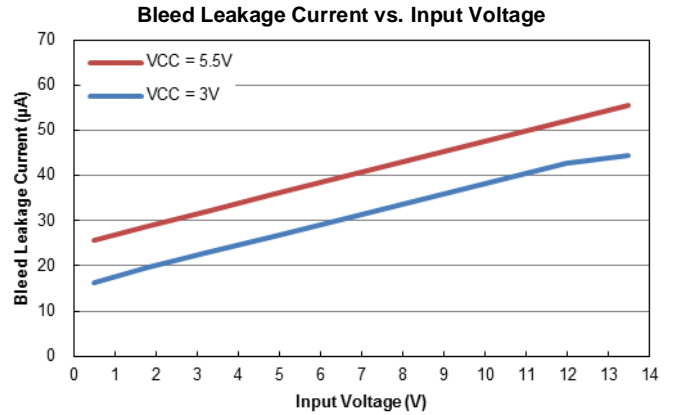
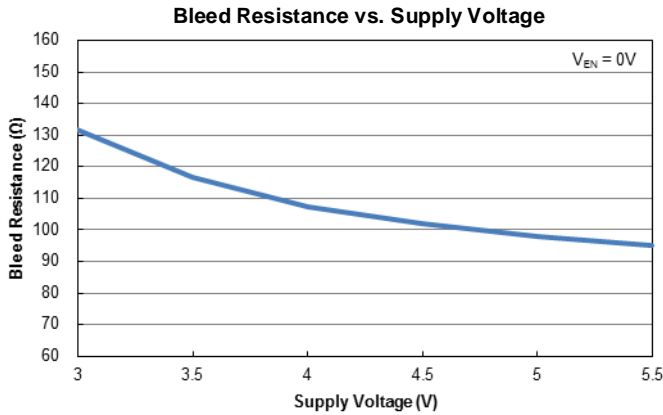
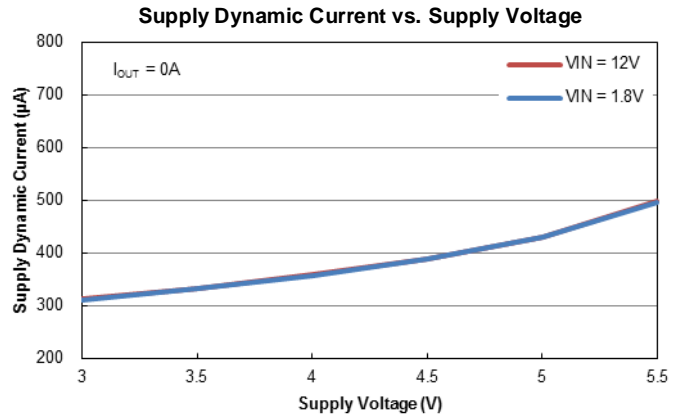
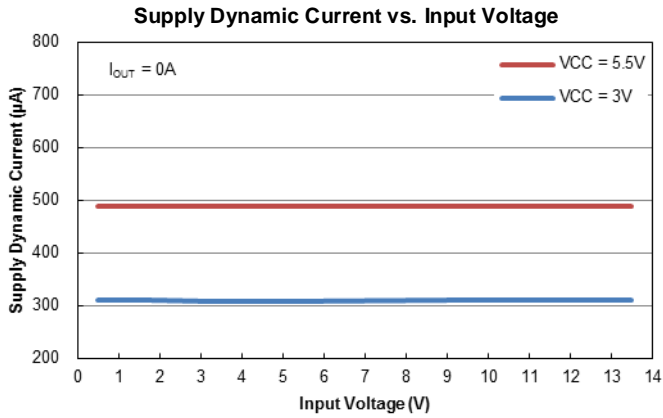


Figure 1 Timing Diagram

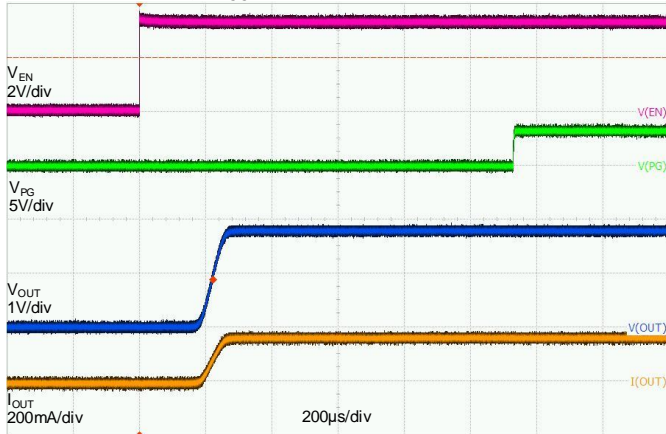
**Performance Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



**Performance Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.) (continued)

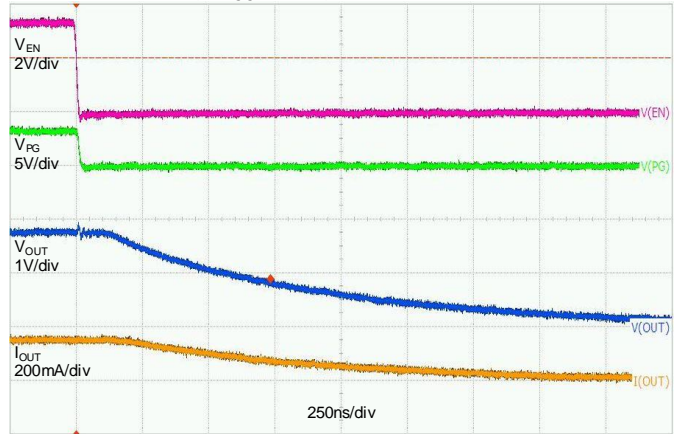
**Turn ON Response**

$V_{IN} = 1.8\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



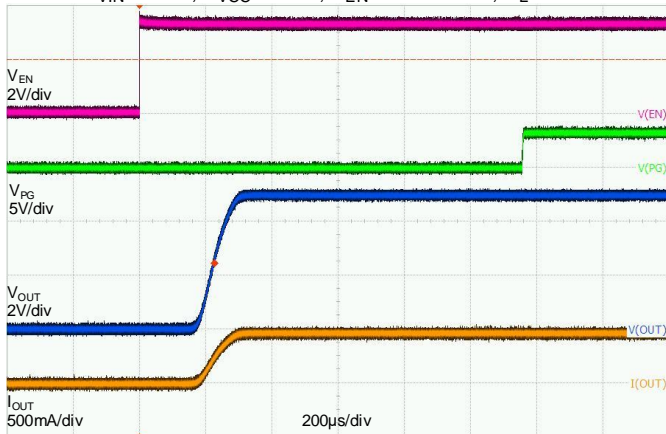
**Turn OFF Response**

$V_{IN} = 1.8\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



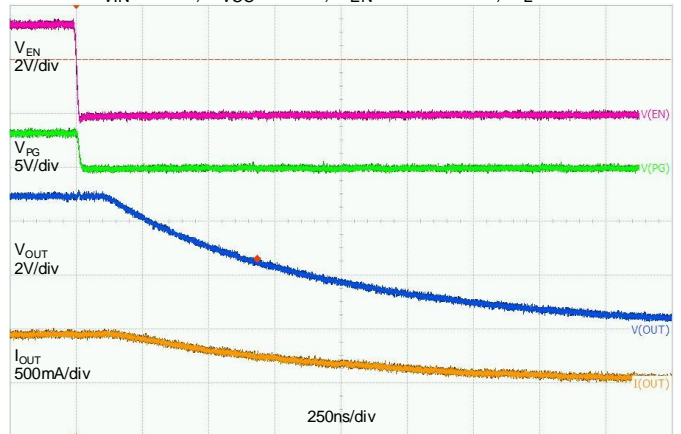
**Turn ON Response**

$V_{IN} = 5.0\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



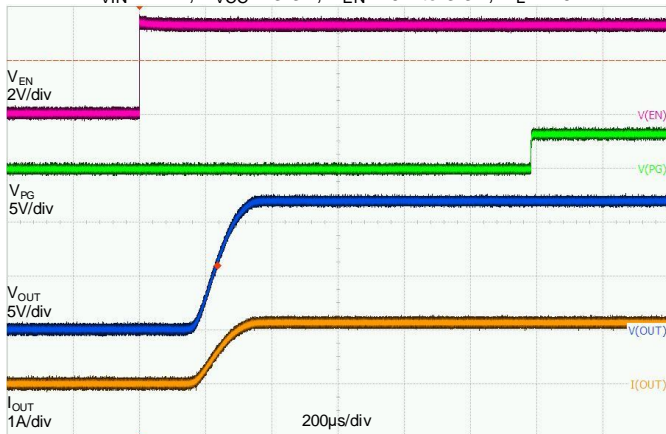
**Turn OFF Response**

$V_{IN} = 5.0\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



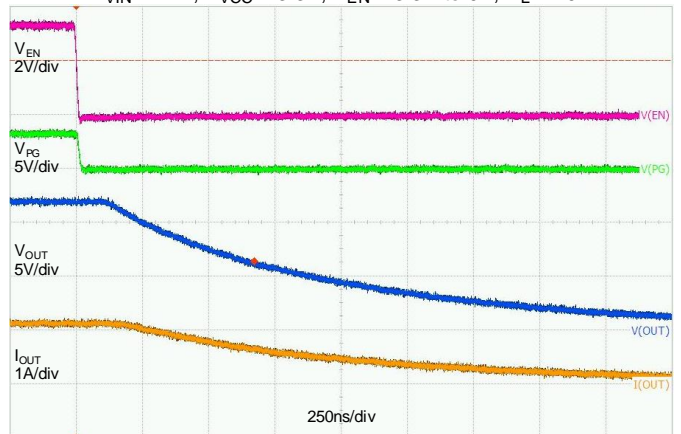
**Turn ON Response**

$V_{IN} = 12\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



**Turn OFF Response**

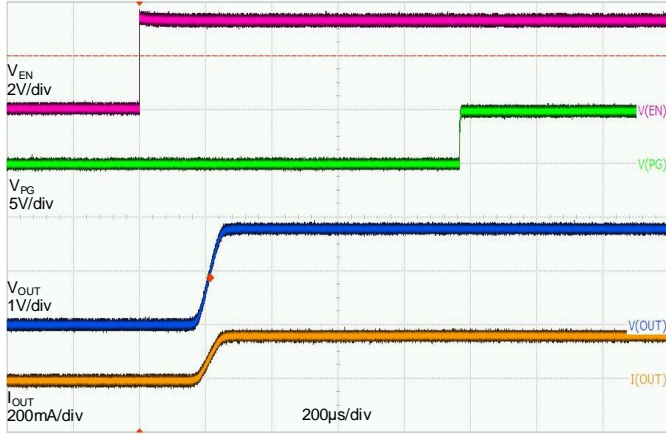
$V_{IN} = 12\text{V}$ ,  $V_{CC} = 3.3\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



**Performance Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.) (continued)

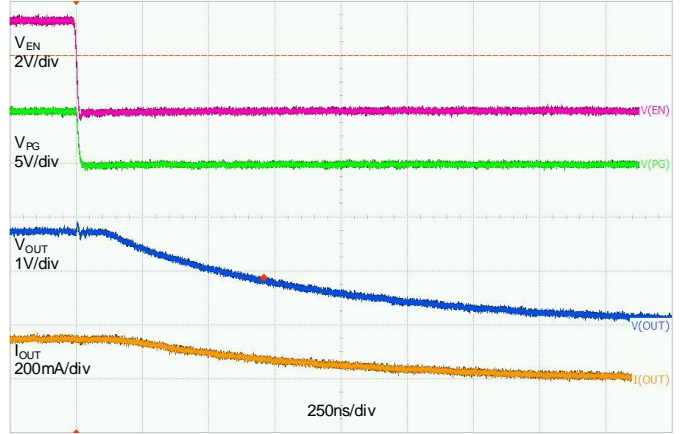
**Turn ON Response**

$V_{IN} = 1.8\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



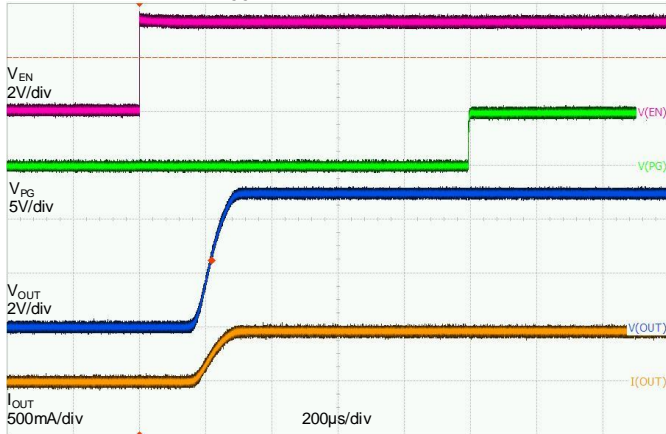
**Turn OFF Response**

$V_{IN} = 1.8\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



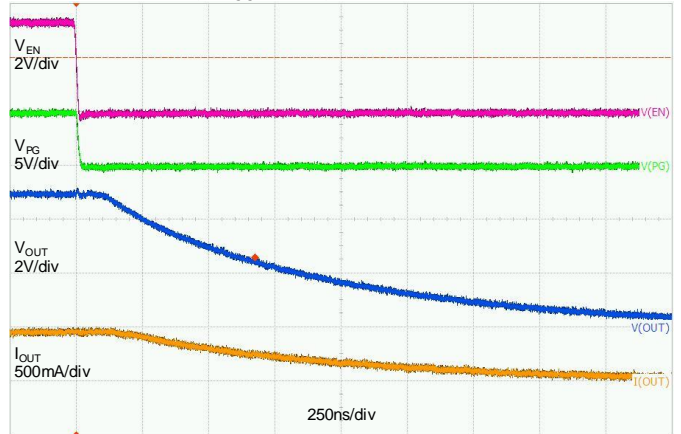
**Turn ON Response**

$V_{IN} = 5.0\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



**Turn OFF Response**

$V_{IN} = 5.0\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



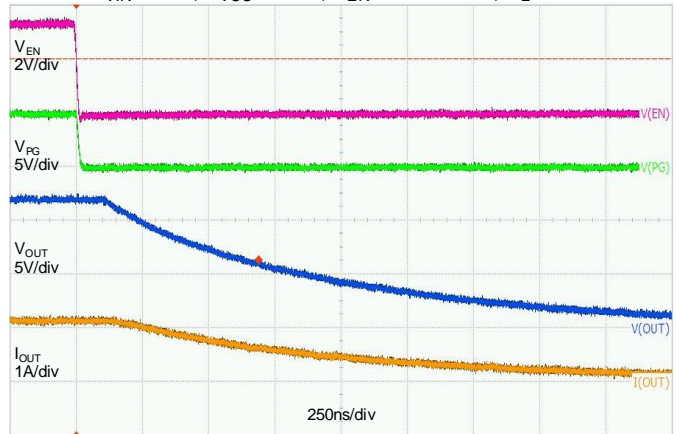
**Turn ON Response**

$V_{IN} = 12\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 0\text{V to } 3.3\text{V}$ ,  $R_L = 10\Omega$



**Turn OFF Response**

$V_{IN} = 12\text{V}$ ,  $V_{CC} = 5.0\text{V}$ ,  $V_{EN} = 3.3\text{V to } 0\text{V}$ ,  $R_L = 10\Omega$



## Application Information

### General Description

The DML3006LFDS is a single channel load switch with a controlled adjustable turn-on and integrated PG indicator in an 8-pin V-DFN2020-8 (Type F) package. The device contains an N-channel MOSFET that can operate over an input voltage range of 0.5V to 13.5V and can support a maximum continuous current of 11A. The wide input voltage range and high current capability enable the device to be used across multiple designs and end equipment. 9mΩ on-resistance minimizes the voltage drop across the load switch and power loss from the load switch.

The controlled rise time for the device greatly reduces inrush current by large bulk load capacitances, thereby reducing or eliminating power supply droop. The adjustable slew rate through SR provides the design flexibility to trade off the inrush current and power up timing requirements. Integrated PG indicator notifies the system about the status of the load switch to facilitate seamless power sequencing. During shutdown, the device has very low leakage current, thereby reducing unnecessary leakages for downstream modules during standby. A 100Ω On-chip resistor also embedded on the BLEED pin of DML3006LFDS for quick discharge of the output when switch is disabled.

### Enable Control

The DML3006LFDS device allows for enabling the MOSFET in an active-high configuration. When the V<sub>CC</sub> supply pin has an adequate voltage applied and the EN pin is at logic high level, the MOSFET is enabled. Similarly, when the EN pin is at logic low level, the MOSFET is disabled. An internal pull down resistor to ground on the EN pin ensures that the MOSFET disabled when not being driven.

### Power sequencing

The DML3006LFDS functions with any power sequence, but the output turn-on delay performance can vary from what is specified. To achieve the specified performance that we recommended power sequence is:

$$V_{CC} \rightarrow V_{IN} \rightarrow V_{EN}$$

### Load Bleed (Quick Discharge)

The DML3006LFDS has an internal bleed discharge device, which used to bleed the charge off from the load to ground after the MOSFET was disabled. The bleed discharge device is enabled whenever the MOSFET is disabled. The MOSFET and the bleed device are never concurrently active.

The BLEED pin must connect to V<sub>OUT</sub> either directly or through an external resistor, R<sub>EXT</sub>. The R<sub>EXT</sub> must not exceed 1kΩ and can be used to increase the total bleed resistance.

Care must be taken to ensure that the power dissipated across R<sub>BLEED</sub> kept at safe level. The maximum continuous power that can be dissipates across R<sub>BLEED</sub> is 0.4W. R<sub>EXT</sub> can be used to decrease the amount of power dissipated across R<sub>BLEED</sub>.

### Power Good

The DML3006LFDS device has a power good output (PG) that can be used to indicate when the gate of the MOSFET is driven high and the switch is on with the on-resistance close to its final value (at the full load condition). The PG pin is an active-high, open-drain output that requires an external pull up resistor, R<sub>PG</sub>, greater than or equal to 1kΩ to an external voltage source, V<sub>TERM</sub>, compatible with input levels of those devices connected to this pin.

The power good output can be used as the enable signal for other active-high devices in the system. This allows for guaranteed by design power sequencing and reduces the number of enable signals needed from the system controller. If the power good feature is not used in the application, the PG pin must be tied to GND.

### Short Circuit Protection

The DML3006LFDS is equipped with short-circuit protection that is used to help protect the part and the system from a sudden high-current event, such as the output, V<sub>OUT</sub>, being shorted to ground. This circuitry is only active when the gate of MOSFET is fully charged.

Once active, the circuitry monitors the difference in the voltage on the V<sub>IN</sub> pin and the voltage on the BLEED pin. In order for the V<sub>OUT</sub> voltage to be monitored through the BLEED pin, it is required that BLEED pin be connected to V<sub>OUT</sub> either directly or through a resistor, R<sub>EXT</sub>, which should not exceed 1kΩ. Once the BLEED pin is connected to V<sub>OUT</sub>, the short-circuit protection will be activated to monitor the voltage drop across the MOSFET.

If the voltage drop across the MOSFET is greater than or equal to the short-circuit protection threshold voltage, the MOSFET is immediately turned off and the load bleed is activated. The part remains latched in this off state until EN is toggled or V<sub>CC</sub> supply voltage is cycled, at which point the MOSFET will be turn-on delay and slew rate. The current through the MOSFET that will cause a short-circuit event can be calculated by dividing the short-circuit protection threshold by expected on-resistance of the MOSFET.



**Application Information** (continued)

**Thermal Shutdown**

The DML3006LFDS is equipped with thermal shutdown protection for internally or externally generated excessive temperatures. This circuitry is disabled when EN is not active to reduce standby current. When an overtemperature condition is detected, the MOSFET is immediately turned off and the load bleed is active.

The part comes out of thermal shutdown when the junction temperature decreases to a safe operating temperature, as dictated by the thermal hysteresis. Upon exiting a thermal shutdown state and if EN remains active, the MOSFET will be turned on in a controlled fashion with the normal output turn-on delay and slew rate.

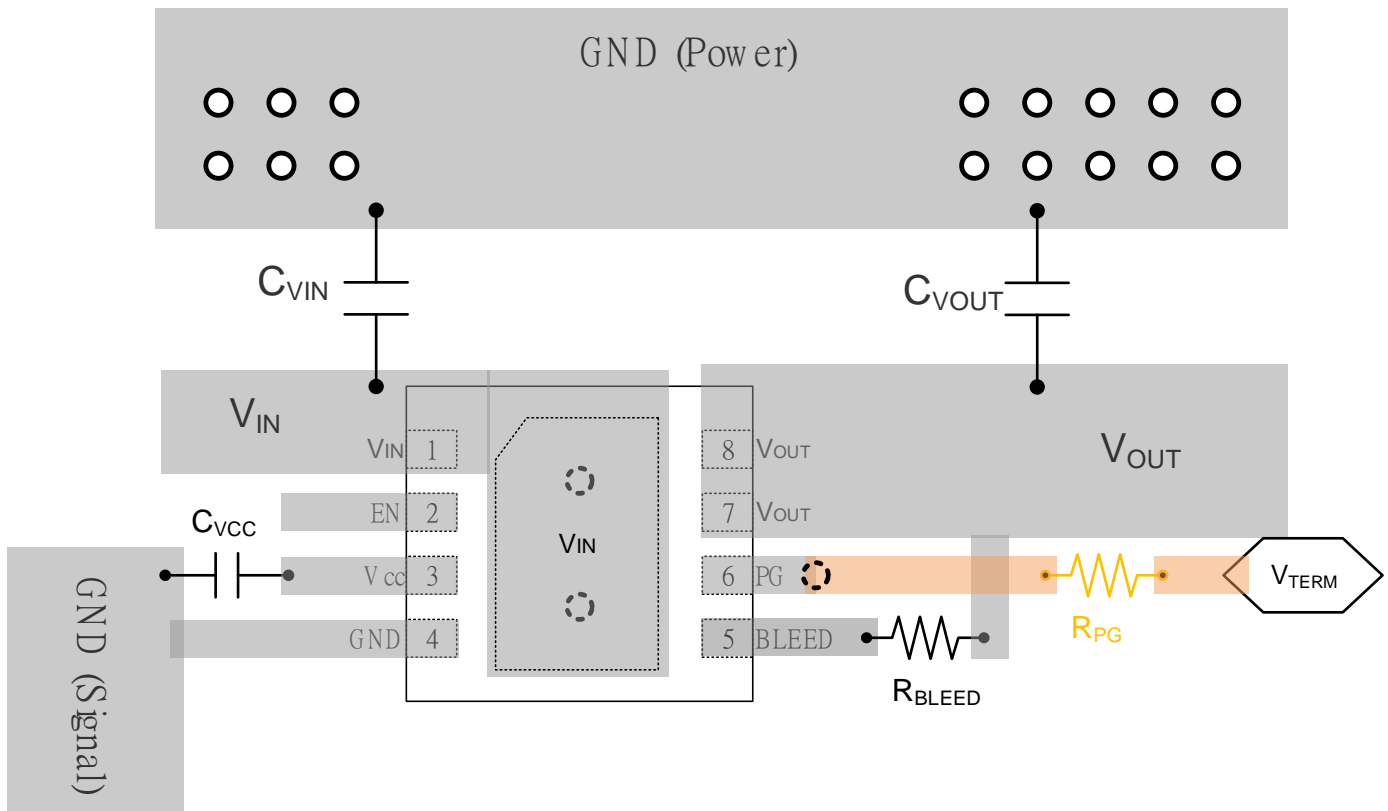
**Undervoltage Lockout**

The DML3006LFDS is also equipped with undervoltage lockout protection. The DML3006LFDS turns the MOSFET off and activates the load bleed when the input voltage,  $V_{IN}$ , is less than or equal to the undervoltage lockout threshold. This circuitry is disabled when EN is not active to reduce standby current.

If the  $V_{IN}$  voltage rises above the undervoltage lockout threshold and EN remains active, the MOSFET will be turned on in a controlled fashion with the normal output turn-on delay and slew rate.

**PCB Layout Consideration**

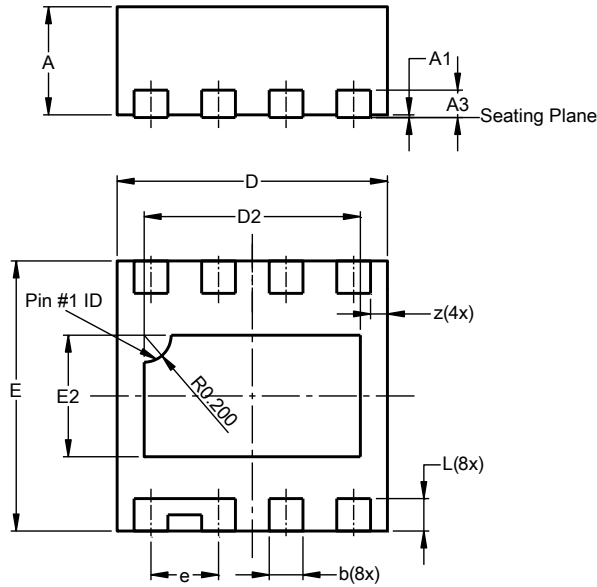
1. Place the input/output capacitors  $C_{VIN}$  and  $C_{VOUT}$  as close as possible to the  $V_{IN}$  and  $V_{OUT}$  pins.
2. The power traces which are  $V_{IN}$  trace,  $V_{OUT}$  trace and GND trace should be short, wide and direct for minimizing parasitic inductance.
3. Place feedback resistance  $R_{BLEED}$  as close as possible to BLEED pin.
4. Place  $C_{VCC}$  capacitor near the device pin.
5. Connect the signal ground to the GND pin, and keep a single connection from GND pin to the power ground behind the input or output capacitors.
6. For better power dissipation, via holes are recommended to connect the exposed pad's landing area to a large copper polygon on the other side of the printed circuit board. The copper polygons and exposed pad shall connect to  $V_{IN}$  pin on the printed circuit board.



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN2020-8 (Type F)

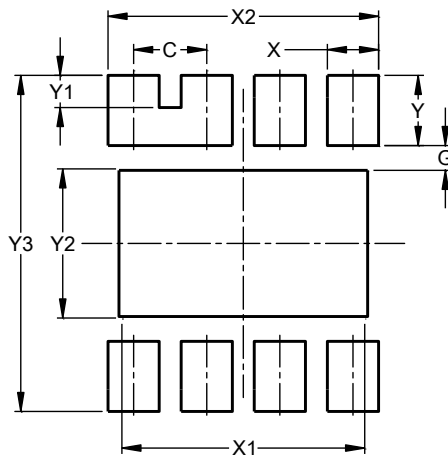


V-DFN2020-8 (Type F)			
Dim	Min	Max	T p
A	0.77	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.20	0.30	0.25
D	1.95	2.05	2.00
D2	1.50	1.70	1.60
E	1.95	2.05	2.00
E2	0.80	1.00	0.90
e	--	--	0.50
L	0.19	0.29	0.24
z	--	--	0.125
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN2020-8 (Type F)



Dimensions	Value (in mm)
C	0.500
G	0.170
X	0.350
X1	1.660
X2	1.850
Y	0.480
Y1	0.220
Y2	1.020
Y3	2.300

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